

G Amarnath

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

108
citations

1684188

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h-index

1720034

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26
all docs

26
docs citations

26
times ranked

66
citing authors

#	ARTICLE	IF	CITATIONS
1	Designing of RF-MEMS Capacitive Contact Shunt Switch and Its Simulation for S-band Application. Lecture Notes in Electrical Engineering, 2022, , 439-448.	0.4	1
2	Design and Analysis of FEM Novel X-Shaped Broadband Linear Piezoelectric Energy Harvester. Lecture Notes in Electrical Engineering, 2022, , 407-416.	0.4	0
3	Numerical Simulation-Based Comparative Study of FinFET and MOSFET with Gallium Oxide. Lecture Notes in Electrical Engineering, 2022, , 265-272.	0.4	0
4	Flicker Noise Analysis of Non-uniform Body TFET with Dual Material Source (NUTFET-DMS). Lecture Notes in Electrical Engineering, 2022, , 247-253.	0.4	0
5	AlInN/GaN HEMT on Silicon Substrate with GD-Field-Plate: Modelling and Simulation of Electric-Field and Breakdown-Voltage Characteristics. Silicon, 2022, 14, 10327-10335.	3.3	4
6	Threshold-Voltage Analytical-Model Development for Junction-less-Double-Gate FETs. , 2021, , .		0
7	Artificial Neural Network Based Statistical-Analysis of High-Speed-Interconnect-Systems. , 2021, , .		0
8	Employing Analog Circuits by Neural-Network based Multi-Layer-Perceptron. , 2021, , .		1
9	Noise and IM3 Harmonics Cancelling in Two-Stage Wideband Differential LNA. , 2021, , .		0
10	Utilizing Analog Circuits by Neural-Network based Multi-Layer-Perceptron. , 2021, , .		0
11	Analysis of Temperature Effect on Small-Signal- Equivalent-Circuit Parameters for AlInN/GaN MOS-HEMT. , 2020, , .		0
12	TCAD-based Comparative Study of Gallium-Oxide based FinFET and MOSFET. , 2020, , .		1
13	Analytical Model Development for Channel Potential in Junction-less Double-Gate FETs. , 2020, , .		2
14	Developement of Threshold-Voltage Analytical-Model for Double-Gate-Junction-less FETs. , 2020, , .		0
15	Modeling and simulation of DC and microwave characteristics of AlInN(AlGaIn)/AlN/GaN MOSHEMTs with different gate lengths. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2019, 32, e2456.	1.9	19
16	Modeling and simulation of 2DEG density and intrinsic capacitances in AlInN/GaN MOSHEMT. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2018, 31, e2268.	1.9	12
17	Microwave frequency small-signal equivalent circuit parameter extraction for AlInN/GaN MOSHEMT. International Journal of RF and Microwave Computer-Aided Engineering, 2018, 28, e21179.	1.2	13
18	Small-signal model parameter extraction of E-mode N-polar GaN MOS-HEMT using optimization algorithms and its comparison. Journal of Semiconductors, 2018, 39, 074001.	3.7	12

#	ARTICLE	IF	CITATIONS
19	Analytical Model Development for Unified 2D Electron Gas Sheet Charge Density of AlInN/GaN MOSHEMT. International Journal of Electronics and Telecommunications, 2017, 63, 363-368.	0.6	7
20	Electrical characteristics and 2DEG properties of passivated InAlN/AlN/GaN HEMT. , 2015, , .		8
21	374GHz cut-off frequency of ultra thin InAlN/AlN/GaN MIS HEMT. , 2015, , .		5
22	Impact of image preprocessing on face recognition: A comparative analysis. , 2014, , .		7
23	An improved gate capacitance for two dimensional junctionless transistor. , 2014, , .		1
24	Modelling the flood-risk extent using LISFLOOD-FP in a complex watershed: case study of Mundeni Aru River Basin, Sri Lanka. Proceedings of the International Association of Hydrological Sciences, 0, 370, 131-138.	1.0	15